2.5V Drive Nch MOS FET **RJU002N06**

Structure

Silicon N-channel MOS FET

Features

1) Low On-resistance.

2) Low voltage drive (2.5V drive).

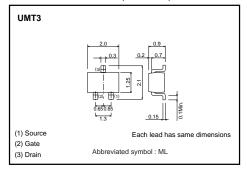
Applications

Switching

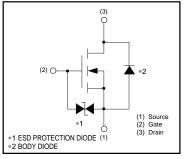
Packaging specifications

| | Package | Taping | |
|-----------|------------------------------|--------|--|
| Туре | Code | T106 | |
| | Basic ordering unit (pieces) | 3000 | |
| RJU002N06 | 0 | | |

•External dimensions (Unit : mm)



Inner circuit



Absolute maximum ratings (Ta=25°C)

| Parameter | | Symbol | Limits | Unit |
|------------------------------|------------|-------------------|-------------|------|
| Drain-source voltage | | VDSS | 60 | V |
| Gate-source voltage | | Vgss | ±12 | V |
| Ducia coment | Continuous | lo | ±200 | mA |
| Drain current | Pulsed | IDP *1 | ±800 | mA |
| Total power dissipation | | P _D *2 | 200 | mW |
| Channel temperature | | Tch | 150 | °C |
| Range of storage temperature | | Tstg | -55 to +150 | °C |
| | | | | |

*1 Pw≤10µs, Duty cycle≤1%
 *2 Each terminal mounted on a recommended land

Thermal resistance

| Parameter | Symbol | Limits | Unit |
|--------------------|------------|--------|------|
| Channel to ambient | Rth(ch-a)* | 625 | °C/W |

* Each terminal mounted on a recommended land

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Transistors

•Electrical characteristics (Ta=25°C)

| Parameter | Symbol | Min. | Тур. | Max. | Unit | Conditions | |
|---|-------------------------|------|------|------|------|--|--|
| Gate-source leakage | I _{GSS} | - | - | ±10 | μΑ | V _{GS} =±12V, V _{DS} =0V | |
| Drain-source breakdown voltage | V(BR) DSS | 60 | - | - | V | I _D = 1mA, V _{GS} =0V | |
| Zero gate voltage drain current | IDSS | - | - | 1 | μΑ | VDS= 60V, VGS=0V | |
| Gate threshold voltage | VGS (th) | 0.5 | - | 1.5 | V | V _{DS} = 10V, I _D = 1mA | |
| Static drain-source on-state resistance | $RDS\left(on ight)^{*}$ | - | 1.6 | 2.3 | Ω | I _D = 200mA, V _{GS} = 4.5V | |
| | | - | 1.7 | 2.4 | Ω | ID= 200mA, VGs= 4V | |
| | | - | 2.2 | 3.1 | Ω | I _D = 200mA, V _{GS} = 2.5V | |
| Forward transfer admittance | Y _{fs} * | 0.1 | - | - | S | V _{DS} = 10V, I _D = 200mA | |
| Input capacitance | Ciss | - | 18 | - | pF | VDS= 10V | |
| Output capacitance | Coss | - | 7 | - | pF | V _{GS} =0V | |
| Reverse transfer capacitance | Crss | - | 5 | - | pF | f=1MHz | |
| Turn-on delay time | t _{d (on)} * | - | 7 | - | ns | Vdd≒ 30V | |
| Rise time | tr * | - | 7 | - | ns | D = 100 mA | |
| Turn-off delay time | td (off) * | - | 12 | - | ns | Vgs= 4V RL=300Ω | |
| Fall time | t _f * | _ | 90 | - | ns | $R_{G}=10\Omega$ | |

•Body diode characteristics (Source-drain) (Ta=25°C)

| Parameter | Symbol | Min. | Тур. | Max. | Unit | Conditions |
|-----------------|--------|------|------|------|------|---|
| Forward voltage | Vsd | - | - | 1.2 | V | I _S = 0.16A, V _{GS} =0V |

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